



Thyristor \ Diode Module

$V_{RRM} = 2 \times 1800 \text{ V}$

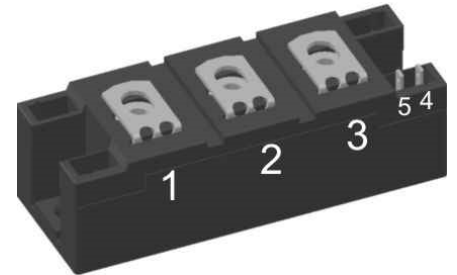
$I_{TAV} = 200 \text{ A}$

$V_T = 1,12 \text{ V}$

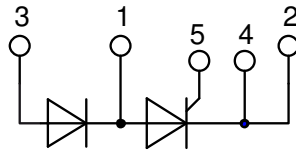
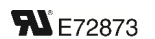
Phase leg

Part number

MCMA200PD1800YB



Backside: isolated



Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al₂O₃-ceramic

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: Y4

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

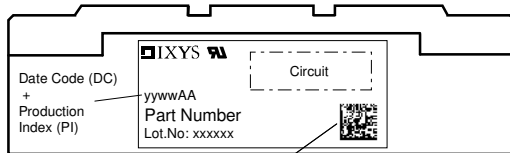
Disclaimer Notice

Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at www.littelfuse.com/disclaimer-electronics.

| Thyristor | | | | Ratings | | | |
|----------------|--|---|-------------------------|---------|-------|-------------------|--|
| Symbol | Definition | Conditions | min. | typ. | max. | Unit | |
| $V_{RSM/DSM}$ | max. non-repetitive reverse/forward blocking voltage | $T_{VJ} = 25^{\circ}C$ | | | 1900 | V | |
| $V_{RRM/DRM}$ | max. repetitive reverse/forward blocking voltage | $T_{VJ} = 25^{\circ}C$ | | | 1800 | V | |
| I_{RD} | reverse current, drain current | $V_{R/D} = 1800 V$ | $T_{VJ} = 25^{\circ}C$ | | 300 | μA | |
| | | $V_{R/D} = 1800 V$ | $T_{VJ} = 125^{\circ}C$ | | 10 | mA | |
| V_T | forward voltage drop | $I_T = 200 A$ | $T_{VJ} = 25^{\circ}C$ | | 1,17 | V | |
| | | $I_T = 400 A$ | | | 1,40 | V | |
| | | $I_T = 200 A$ | $T_{VJ} = 125^{\circ}C$ | | 1,12 | V | |
| | | $I_T = 400 A$ | | | 1,41 | V | |
| I_{TAV} | average forward current | $T_C = 85^{\circ}C$ | $T_{VJ} = 140^{\circ}C$ | | 200 | A | |
| $I_{T(RMS)}$ | RMS forward current | 180° sine | | | 315 | A | |
| V_{T0} | threshold voltage | } for power loss calculation only | $T_{VJ} = 140^{\circ}C$ | | 0,83 | V | |
| r_T | slope resistance | | | | 1,43 | m Ω | |
| R_{thJC} | thermal resistance junction to case | | | | 0,17 | K/W | |
| R_{thCH} | thermal resistance case to heatsink | | | 0,09 | | K/W | |
| P_{tot} | total power dissipation | | $T_C = 25^{\circ}C$ | | 680 | W | |
| I_{TSM} | max. forward surge current | $t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$ | $T_{VJ} = 45^{\circ}C$ | | 6,00 | kA | |
| | | $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$ | $V_R = 0 V$ | | 6,48 | kA | |
| | | $t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$ | $T_{VJ} = 140^{\circ}C$ | | 5,10 | kA | |
| | | $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$ | $V_R = 0 V$ | | 5,51 | kA | |
| I^2t | value for fusing | $t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$ | $T_{VJ} = 45^{\circ}C$ | | 180,0 | kA ² s | |
| | | $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$ | $V_R = 0 V$ | | 174,7 | kA ² s | |
| | | $t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$ | $T_{VJ} = 140^{\circ}C$ | | 130,1 | kA ² s | |
| | | $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$ | $V_R = 0 V$ | | 126,3 | kA ² s | |
| C_J | junction capacitance | $V_R = 400V \quad f = 1 \text{ MHz}$ | $T_{VJ} = 25^{\circ}C$ | | 273 | pF | |
| P_{GM} | max. gate power dissipation | $t_p = 30 \mu s$ | $T_C = 140^{\circ}C$ | | 120 | W | |
| | | $t_p = 500 \mu s$ | | | 60 | W | |
| P_{GAV} | average gate power dissipation | | | | 8 | W | |
| $(di/dt)_{cr}$ | critical rate of rise of current | $T_{VJ} = 140^{\circ}C; f = 50 \text{ Hz}$ repetitive, $I_T = 600 A$ | | | 100 | A/ μs | |
| | | $t_p = 200 \mu s; di_G/dt = 0,5 A/\mu s;$ $I_G = 0,5A; V_D = \frac{2}{3} V_{DRM}$ non-repet., $I_T = 200 A$ | | | 1000 | A/ μs | |
| $(dv/dt)_{cr}$ | critical rate of rise of voltage | $V_D = \frac{2}{3} V_{DRM}$ $R_{GK} = \infty$; method 1 (linear voltage rise) | $T_{VJ} = 140^{\circ}C$ | | 1000 | V/ μs | |
| V_{GT} | gate trigger voltage | $V_D = 6 V$ | $T_{VJ} = 25^{\circ}C$ | | 2,5 | V | |
| | | | $T_{VJ} = -40^{\circ}C$ | | 2,6 | V | |
| I_{GT} | gate trigger current | $V_D = 6 V$ | $T_{VJ} = 25^{\circ}C$ | | 150 | mA | |
| | | | $T_{VJ} = -40^{\circ}C$ | | 200 | mA | |
| V_{GD} | gate non-trigger voltage | $V_D = \frac{2}{3} V_{DRM}$ | $T_{VJ} = 125^{\circ}C$ | | 0,2 | V | |
| I_{GD} | gate non-trigger current | | | | 10 | mA | |
| I_L | latching current | $t_p = 30 \mu s$ | $T_{VJ} = 25^{\circ}C$ | | 300 | mA | |
| | | $I_G = 0,5A; di_G/dt = 0,5 A/\mu s$ | | | | | |
| I_H | holding current | $V_D = 6 V \quad R_{GK} = \infty$ | $T_{VJ} = 25^{\circ}C$ | | 200 | mA | |
| t_{gd} | gate controlled delay time | $V_D = \frac{1}{2} V_{DRM}$ | $T_{VJ} = 25^{\circ}C$ | | 2 | μs | |
| | | $I_G = 0,5A; di_G/dt = 0,5 A/\mu s$ | | | | | |
| t_q | turn-off time | $V_R = 100 V; I_T = 200A; V_D = \frac{2}{3} V_{DRM}$ $di/dt = 10 A/\mu s; dv/dt = 20 V/\mu s; t_p = 200 \mu s$ | $T_{VJ} = 125^{\circ}C$ | | 150 | μs | |



| Package Y4 | | | | Ratings | | | |
|---------------|--|----------------------|-------------------------------------|---------|------|------|--|
| Symbol | Definition | Conditions | min. | typ. | max. | Unit | |
| I_{RMS} | RMS current | per terminal | | | 300 | A | |
| T_{VJ} | virtual junction temperature | | -40 | | 140 | °C | |
| T_{op} | operation temperature | | -40 | | 125 | °C | |
| T_{stg} | storage temperature | | -40 | | 125 | °C | |
| Weight | | | | | 131 | g | |
| M_D | mounting torque | | 2,25 | | 2,75 | Nm | |
| M_T | terminal torque | | 4,5 | | 5,5 | Nm | |
| $d_{Spp/APP}$ | creepage distance on surface striking distance through air | terminal to terminal | 14,0 | 10,0 | | mm | |
| $d_{Spb/APb}$ | | terminal to backside | 16,0 | 16,0 | | mm | |
| V_{ISOL} | isolation voltage | t = 1 second | 50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA | 4800 | | V | |
| | | t = 1 minute | | 4000 | | V | |



Data Matrix: part no. (1-19), DC + PI (20-25), lot.no.# (26-31), blank (32), serial no.# (33-36)

Part description

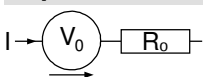
- M = Module
- C = Thyristor (SCR)
- M = Thyristor
- A = (up to 1800V)
- 200 = Current Rating [A]
- PD = Phase leg
- 1800 = Reverse Voltage [V]
- YB = Y4-M6

| Ordering | Ordering Number | Marking on Product | Delivery Mode | Quantity | Code No. |
|----------|-----------------|--------------------|---------------|----------|----------|
| Standard | MCMA200PD1800YB | MCMA200PD1800YB | Box | 6 | |

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 140^{\circ}C$

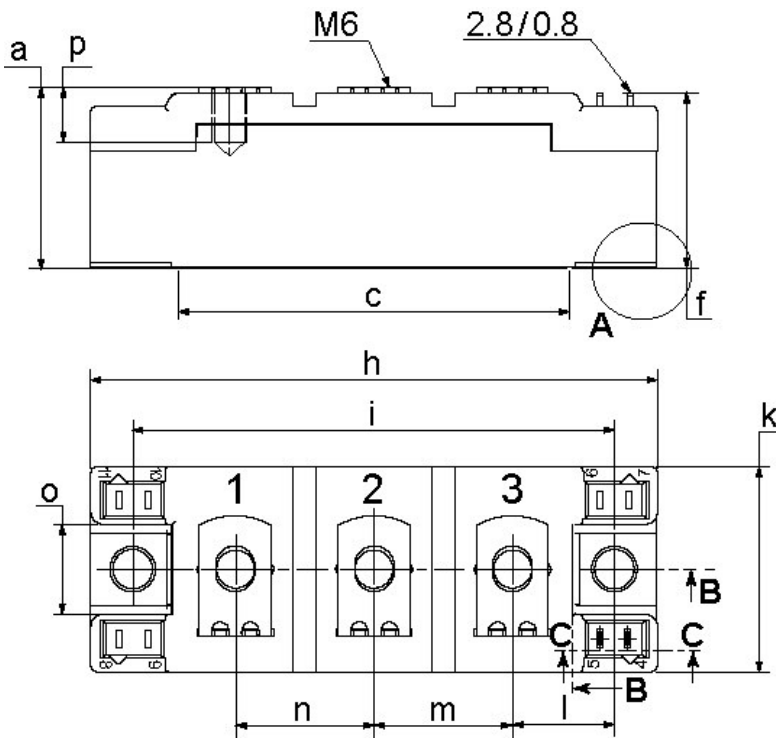


Thyristor

| | | | |
|--------------|--------------------|------|----|
| $V_{0\ max}$ | threshold voltage | 0,83 | V |
| $R_{0\ max}$ | slope resistance * | 0,8 | mΩ |

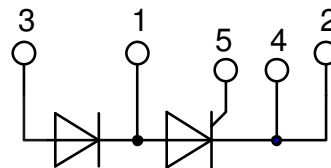
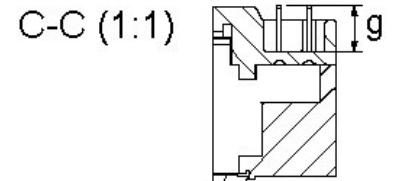
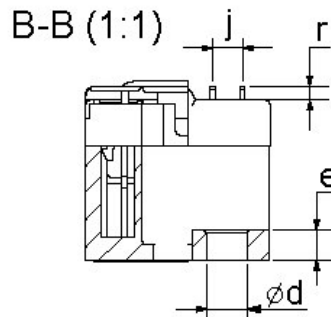
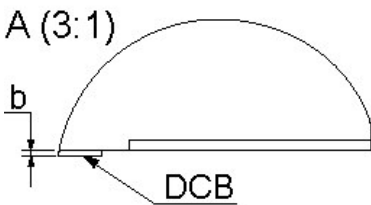


Outlines Y4



| Dim. | MIN [mm] | MAX [mm] | MIN [inch] | MAX [inch] |
|------|-----------|----------|------------|------------|
| a | 30.0 | 30.6 | 1.181 | 1.205 |
| b | typ. 0.25 | | typ. 0.010 | |
| c | 64.0 | 65.0 | 2.520 | 2.559 |
| d | 6.5 | 7.0 | 0.256 | 0.275 |
| e | 4.9 | 5.1 | 0.193 | 0.201 |
| f | 28.6 | 29.2 | 1.126 | 1.150 |
| g | 7.3 | 7.7 | 0.287 | 0.303 |
| h | 93.5 | 94.5 | 3.681 | 3.720 |
| i | 79.5 | 80.5 | 3.130 | 3.169 |
| j | 4.8 | 5.2 | 0.189 | 0.205 |
| k | 33.4 | 34.0 | 1.315 | 1.339 |
| l | 16.7 | 17.3 | 0.657 | 0.681 |
| m | 22.7 | 23.3 | 0.894 | 0.917 |
| n | 22.7 | 23.3 | 0.894 | 0.917 |
| o | 14.0 | 15.0 | 0.551 | 0.591 |
| p | typ. 10.5 | | typ. 0.413 | |
| r | 1.8 | 2.4 | 0.071 | 0.041 |

Optional accessories for modules
Keyed gate/cathode twin plugs with wire length = 350 mm, gate = white, cathode = red
Type ZY 180L (L = Left for pin pair 4/5) UL 758, style 3751



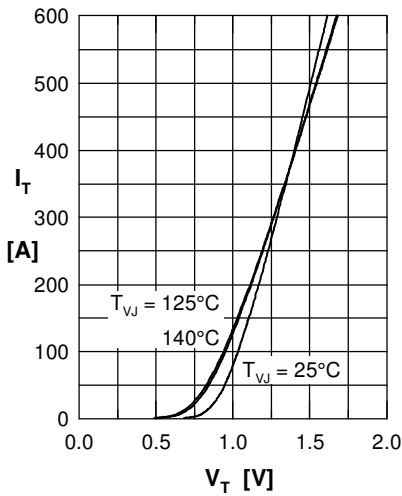
Thyristor


Fig. 1 Forward current vs. voltage drop per thyristor

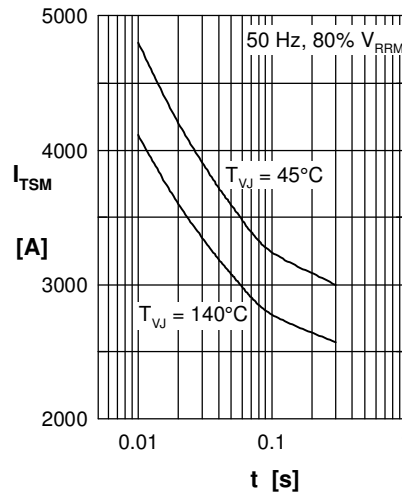


Fig. 2 Surge overload current vs. time per thyristor

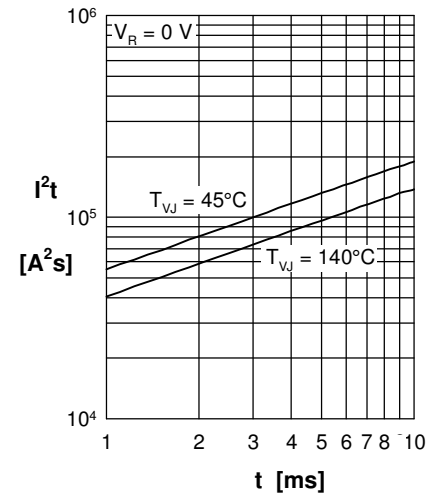
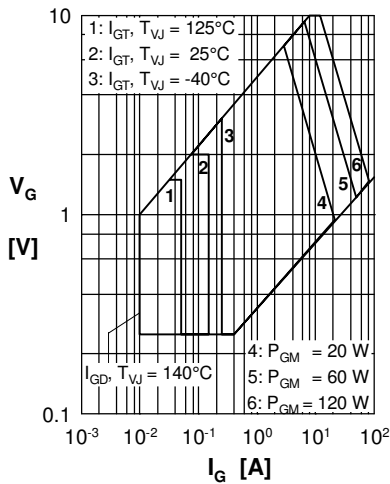

 Fig. 3 I^2t vs. time per thyristor


Fig. 4 Gate voltage & gate current

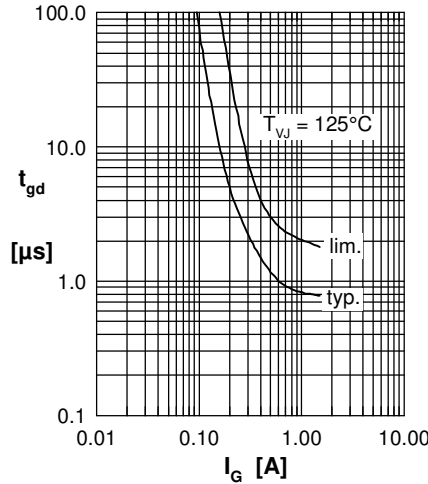
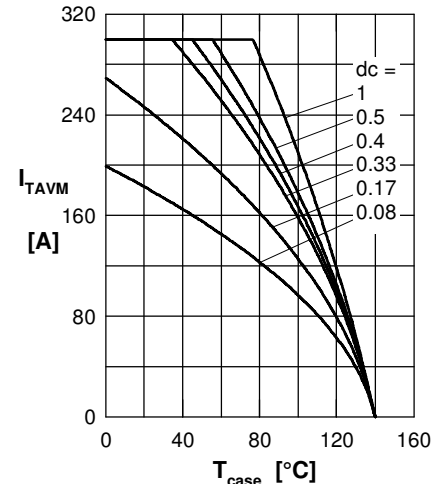

 Fig. 5 Gate controlled delay time t_{gd}


Fig. 6 Max. forward current vs. case temperature per thyristor.

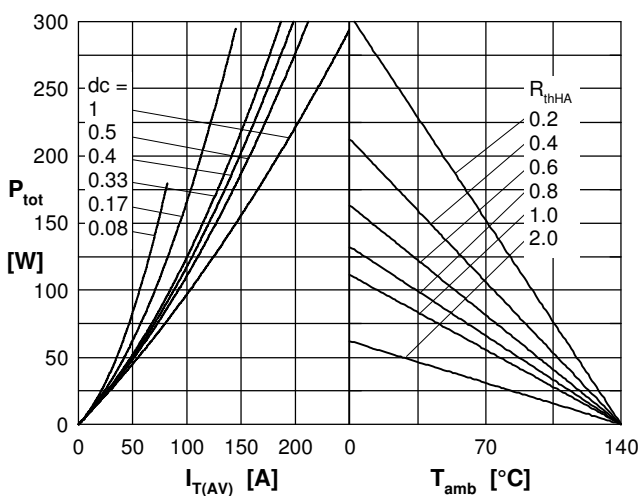


Fig. 7 Power dissipation vs. forward current and ambient temperature per thyristor

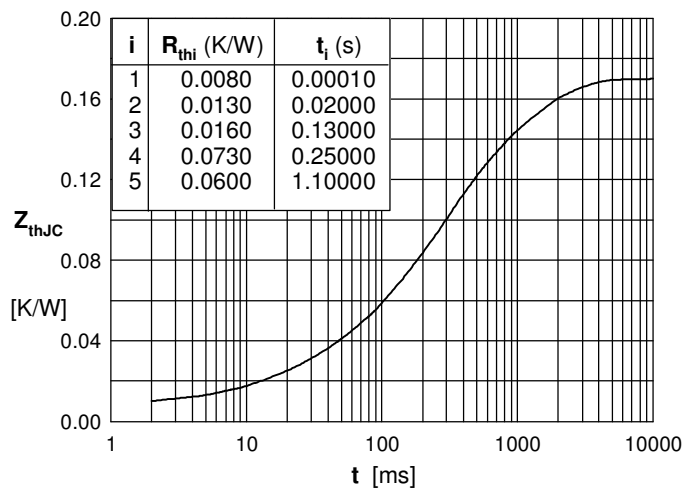


Fig. 8 Transient thermal impedance junction to case vs. time per thyristor